

60V P-CHANNEL ENHANCEMENT MODE MOSFET
Product Summary

BV _{DSS}	R _{DS(on)}	I _D T _A = +25°C
-60V	125mΩ @ V _{GS} = -10V	-4.3A
	190mΩ @ V _{GS} = -4.5V	-3.5A

Description and Applications

This MOSFET is designed to minimize the on-state resistance yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

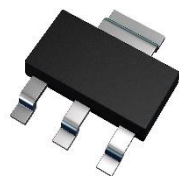
Features and Benefits

- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <https://www.diodes.com/quality/product-definitions/>**
- **An Automotive-Compliant Part is Available Under Separate Datasheet (ZXMP6A17GQ)**

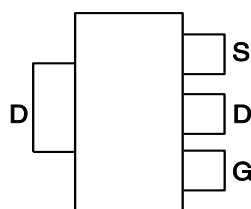
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 Ⓔ3
- Weight: 0.112 grams (Approximate)

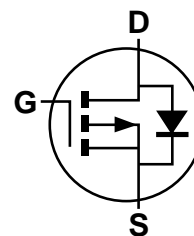
SOT223 (Type DN)



Top View



Pin Out - Top View



Equivalent Circuit

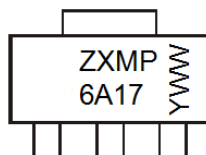
Ordering Information (Note 4)

Part Number	Case	Packaging
ZXMP6A17GTA	SOT223 (Type DN)	1,000/Tape & Reel
ZXMP6A17GTC	SOT223 (Type DN)	4,000/ Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

SOT223 (Type DN)



ZXMP6A17 = Product Type Marking Code
 YWW = Date Code Marking
 Y or \bar{Y} = Year (ex: 1 = 2021)
 WW or \bar{WW} = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

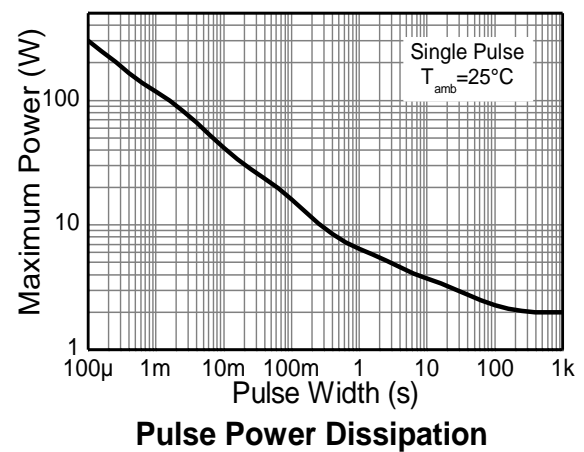
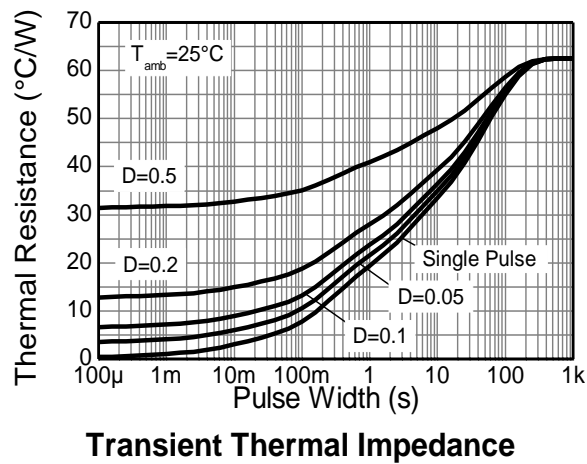
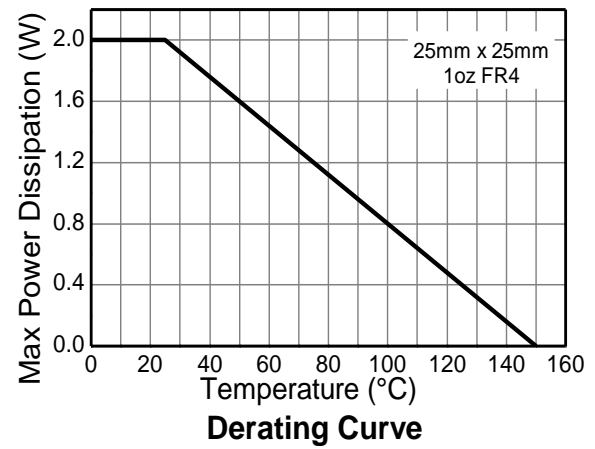
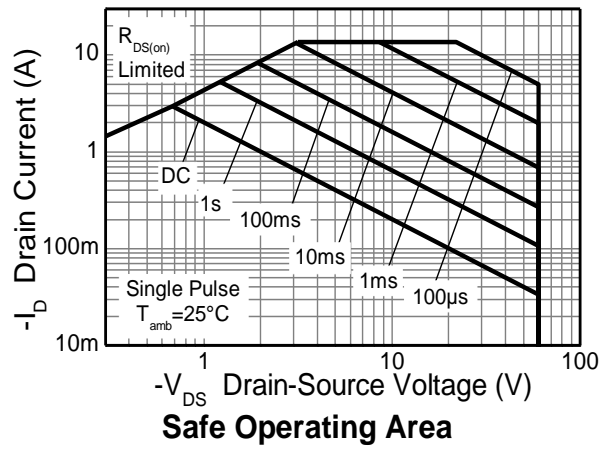
Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current	V _{GS} = 10V	(Note 6)	I _D	-4.3	A
		T _A = +70°C (Note 6)		-3.5	
		(Note 5)		-3.0	
Pulsed Drain Current	V _{GS} = 10V	(Note 7)	I _{DM}	-13.7	A
Continuous Source Current (Body Diode)		(Note 6)	I _S	-4.3	A
Pulsed Source Current (Body Diode)		(Note 7)	I _{SM}	-13.7	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P _D	2.0	W
	(Note 6)		16	
Linear Derating Factor	(Note 5)	R _{θJA}	3.9	mW/°C
	(Note 6)		31	
Thermal Resistance, Junction to Ambient	(Note 5)	R _{θJA}	62.5	°C/W
	(Note 6)		32.0	
Thermal Resistance, Junction to Lead	(Note 8)	R _{θJL}	9.8	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

- Notes:
- For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 - Same as Note 5, except the device is measured at t ≤ 10sec.
 - Same as Note 5, except the device is pulsed with D = 0.02 and pulse width 300μs. The pulse current is limited by the maximum junction temperature.
 - Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics



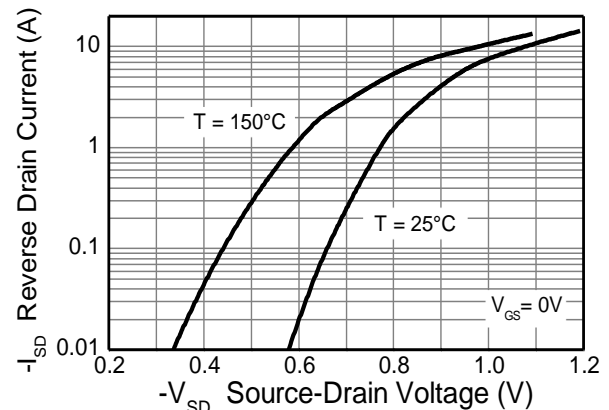
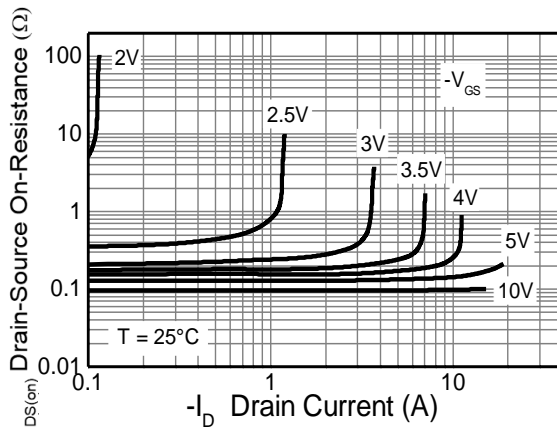
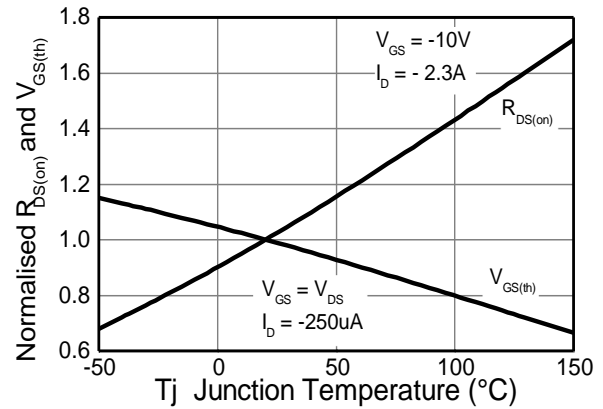
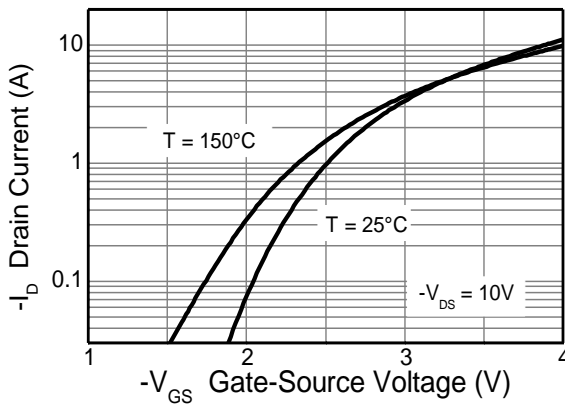
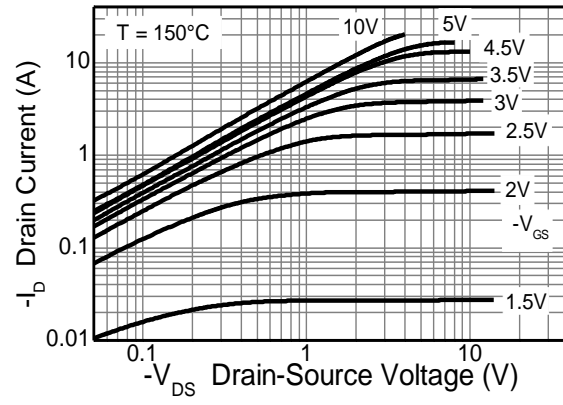
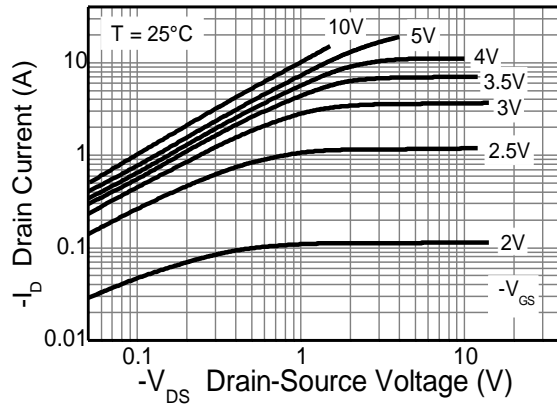
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	—	V	I _D = -250μA, V _{GS} = 0V	
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-0.5	μA	V _{DS} = -60V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	-1.0	—	—	V	I _D = -250μA, V _{DS} = V _{GS}	
Static Drain-Source On-Resistance (Note 9)	R _{DS(ON)}	—	96	125	mΩ	V _{GS} = -10V, I _D = -2.2A	
			120	190		V _{GS} = -4.5V, I _D = -1.8A	
Forward Transconductance (Notes 9 & 10)	g _{fs}	—	4.7	—	S	V _{DS} = -15V, I _D = -2.2A	
Diode Forward Voltage (Note 9)	V _{SD}	—	-0.85	-0.95	V	I _S = -2.0A, V _{GS} = 0V, T _J = +25°C	
Reverse Recovery Time (Note 10)	t _{rr}		25.1	—	ns	I _S = -1.7A, di/dt = 100A/μs, T _J = +25°C	
Reverse Recovery Charge (Note 10)	Q _{rr}	—	27.2	—	nC		
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	—	637	—	pF	V _{DS} = -30V, V _{GS} = 0V f = 1MHz	
Output Capacitance	C _{oss}	—	70.0	—	pF		
Reverse Transfer Capacitance	C _{rss}	—	53.0	—	pF		
Total Gate Charge (Note 11)	Q _g	—	9.0	—	nC	V _{GS} = -4.5V	V _{DS} = -30V I _D = -2.2A
Total Gate Charge (Note 11)	Q _g	—	17.7	—	nC	V _{GS} = -10V	
Gate-Source Charge (Note 11)	Q _{gs}	—	1.6	—	nC		
Gate-Drain Charge (Note 11)	Q _{gd}	—	4.4	—	nC		
Turn-On Delay Time (Note 11)	t _{D(on)}	—	2.6	—	ns	V _{DD} = -30V, V _{GS} = -10V I _D = -1A, R _G ≅ 6.0Ω	
Turn-On Rise Time (Note 11)	t _r	—	3.4	—	ns		
Turn-Off Delay Time (Note 11)	t _{D(off)}	—	26.2	—	ns		
Turn-Off Fall Time (Note 11)	t _f	—	11.3	—	ns		

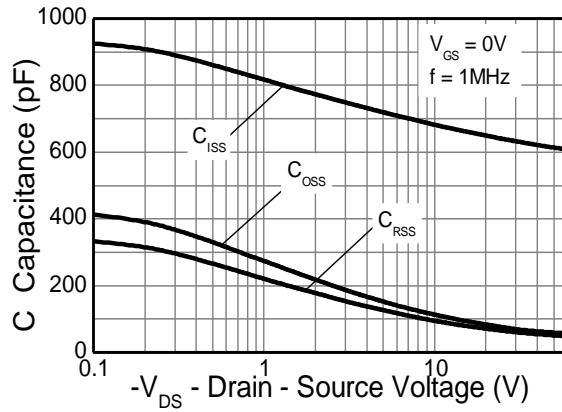
Notes:

9. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%.
10. For design aid only, not subject to production testing.
11. Switching characteristics are independent of operating junction temperatures.

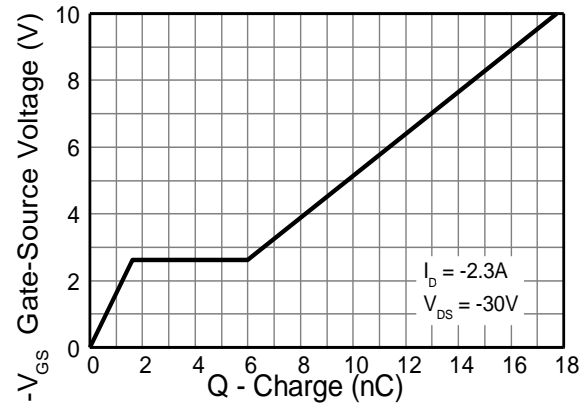
Typical Characteristics



Typical Characteristics (continued)

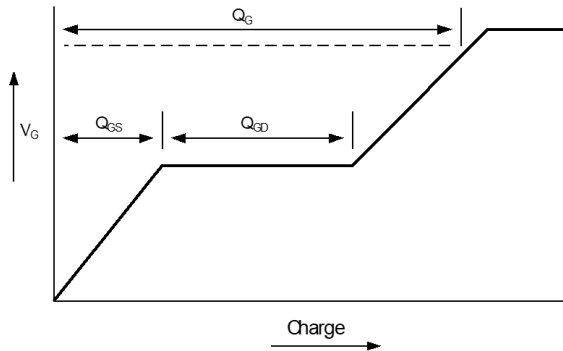


Capacitance v Drain-Source Voltage

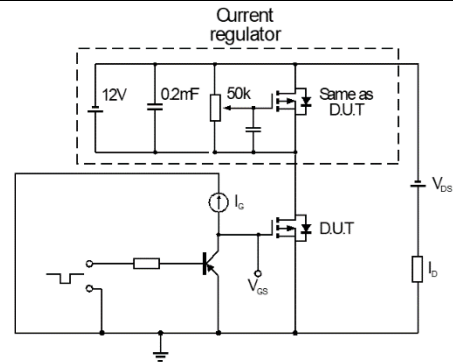


Gate-Source Voltage v Gate Charge

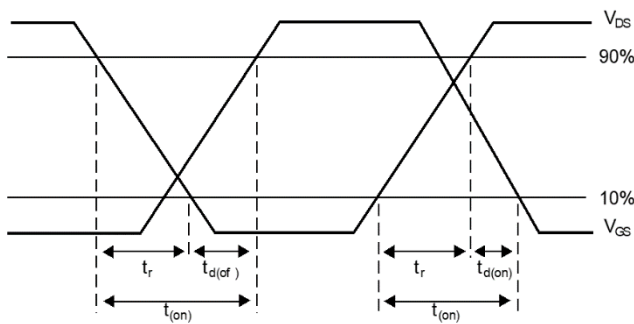
Test Circuits



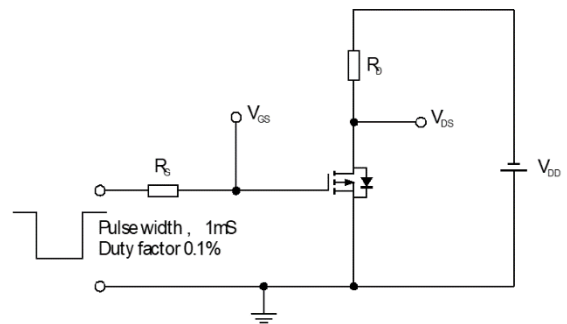
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

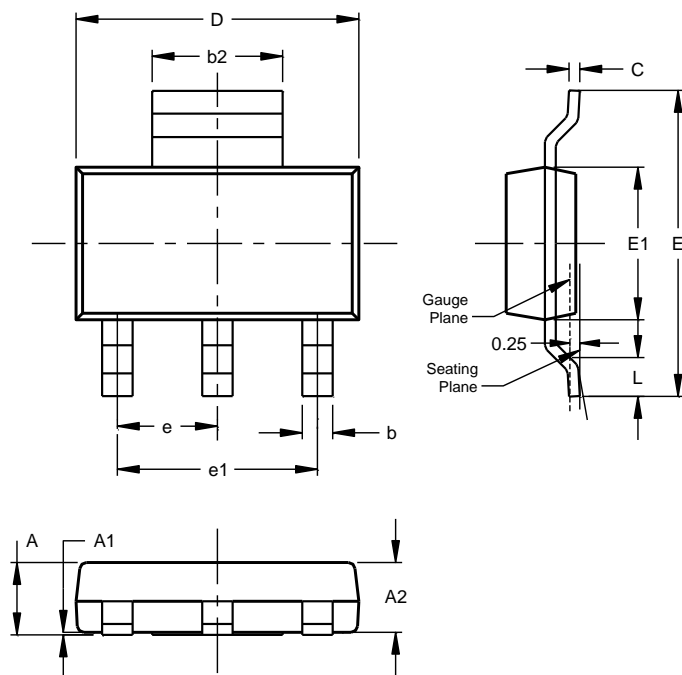


Switching time test circuit

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type DN)

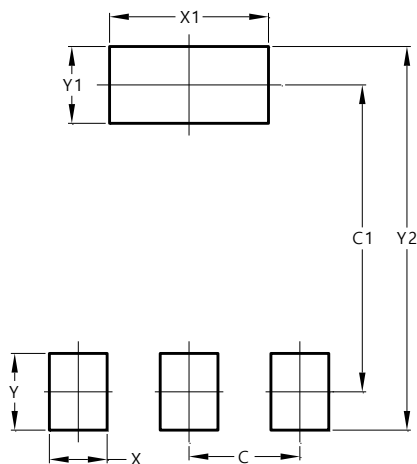


SOT223 (Type DN)			
Dim	Min	Max	Typ
A	--	1.70	--
A1	0.01	0.15	--
A2	1.50	1.68	1.60
b	0.60	0.80	0.70
b2	2.90	3.10	--
c	0.20	0.32	--
D	6.30	6.70	--
E	6.70	7.30	--
E1	3.30	3.70	--
e	--	--	2.30
e1	--	--	4.60
L	0.85	--	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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